



STGP10N60L

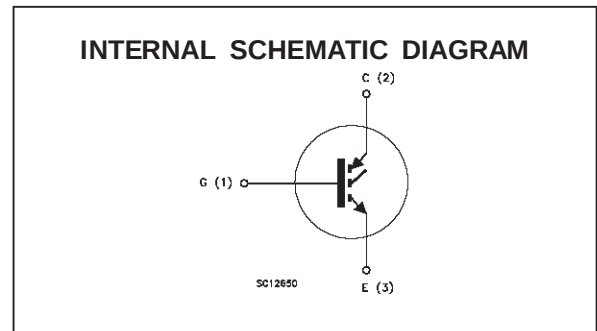
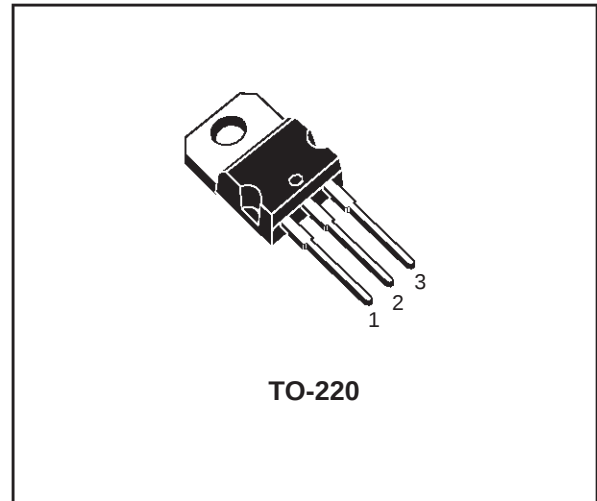
N-CHANNEL 10A - 600V - TO-220 LOGIC LEVEL IGBT

TYPE	V _{CES}	V _{CE(sat)}	I _C
STGP10N60L	600 V	< 1.95 V	10 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- VERY LOW ON-VOLTAGE DROP (V_{cesat})
- LOW THRESHOLD VOLTAGE (LOGIC LEVEL INPUT)
- HIGH CURRENT CAPABILITY
- OFF LOSSES INCLUDE TAIL CURRENT

APPLICATIONS

- ELECTRONIC IGNITION
- LIGHT DIMMER
- STATIC RELAYS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600	V
V _{ECR}	Reverse Battery Protection	25	V
V _{GE}	Gate-Emitter Voltage	± 15	V
I _C	Collector Current (continuous) at T _c = 25 °C	25	A
I _C	Collector Current (continuous) at T _c = 100 °C	20	A
I _{CM} (•)	Collector Current (pulsed)	100	A
P _{tot}	Total Dissipation at T _c = 25 °C	125	W
	Derating Factor	1	W/°C
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

STGP10N60L

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.1	°C/W

ELECTRICAL CHARACTERISTICS (T_j = - 40 to 150 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(ces)}	Collector-Emitter Breakdown Voltage	I _C = 250 μA V _{GE} = 0	600			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{CE} = Max Rating T _j = 25 °C V _{CE} = Max Rating T _j = 125 °C			25 100	μA μA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ± 15 V V _{CE} = 0			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} I _C = 250 μA V _{CE} = V _{GE} I _C = 250 μA T _j = 25 °C	0.6 1.0		2.4 2.0	V V
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	V _{GE} = 4.5 V I _C = 8 A T _j = - 40 °C V _{GE} = 4.5 V I _C = 9.5 A T _j = 25 °C V _{GE} = 4.5 V I _C = 8 A T _j = 150 °C		1.5 1.4 1.25	2.0	V V V
I _C	Collector Current	V _{GE} = 4.5 V V _{CE} = 7 V	15	45		A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs}	Forward Transconductance	V _{CE} = 25 V I _C = 8 A T _j = 25 °C	7	12		S
C _{ies} C _{oes} C _{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{CE} = 25 V f = 1 MHz V _{GE} = 0		1800 120 19	2600 165 26	pF pF pF
Q _G	Gate Charge	V _{CE} = 400 V I _C = 8 A V _{GE} = 5 V		30		nC

FUNCTIONAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CL}	Latching Current	V _{clamp} = 480 V dV/dt = 200 V/μs T _j = 125 °C	20			A
E _{CF}	Forward Clamping Energy	T _{start} = 55 °C V _{clamp} = 480 V I _C = 10 A L = 4.2 mH - Single Pulse	210			mJ
E _{AR}	Reverse Avalanche Energy		10			mJ

ELECTRICAL CHARACTERISTICS (continued)
SWITCHING ON

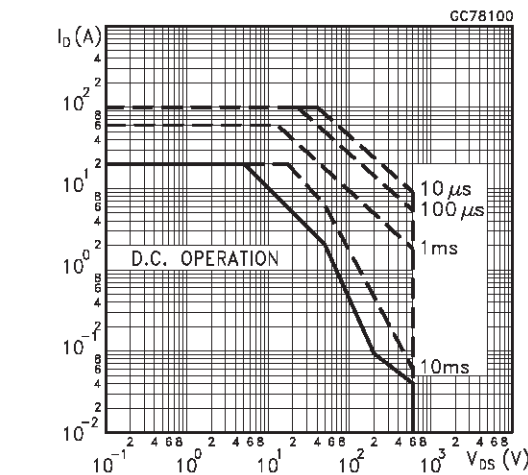
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Delay Time	$V_{CC} = 480\text{ V}$		0.7		μs
t_r	Rise Time	$I_C = 8\text{ A}$ $V_{GE} = 5\text{ V}$ $R_G = 1\text{ K}\Omega$		1.9		μs
$(di/dt)_{on}$	Turn-on Current Slope	$V_{CC} = 480\text{ V}$ $R_G = 1\text{ K}\Omega$ $T_j = 125\text{ }^\circ\text{C}$		5		$\text{A}/\mu\text{s}$
E_{on}	Turn-on Switching Losses			2.5		mJ

SWITCHING OFF

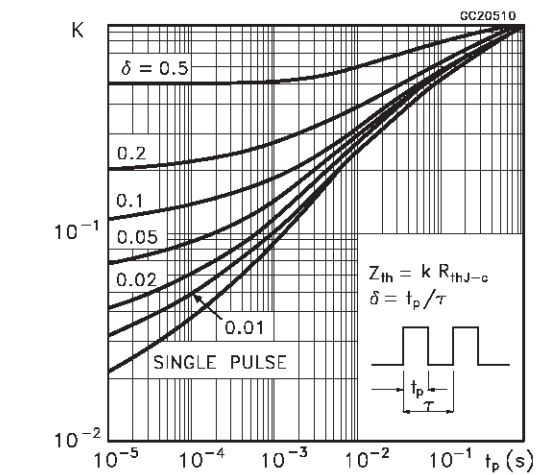
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c	Cross-Over Time	$V_{CC} = 480\text{ V}$ $R_{GE} = 1\text{ K}\Omega$ $T_j = 25\text{ }^\circ\text{C}$		4		μs
$t_r(V_{off})$	Off Voltage Rise Time	$I_C = 8\text{ A}$ $V_{GE} = 5\text{ V}$		2.5		μs
t_f	Fall Time			1.5		μs
$E_{off}(^{**})$	Turn-off Switching Loss			9.0		mJ
t_c	Cross-Over Time	$V_{CC} = 480\text{ V}$ $R_{GE} = 1\text{ K}\Omega$ $T_j = 125\text{ }^\circ\text{C}$		6		μs
$t_r(V_{off})$	Off Voltage Rise Time	$I_C = 8\text{ A}$ $V_{GE} = 5\text{ V}$		3.3		μs
t_f	Fall Time			2.5		μs
$E_{off}(^{**})$	Turn-off Switching Loss			10.8		mJ

(•) Pulse width limited by safe operating area
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %
(**) Losses Include Also The Tail (Jedec Standardization)

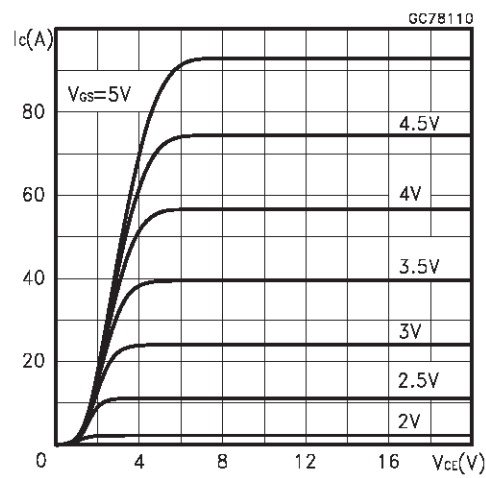
Safe Operating Area



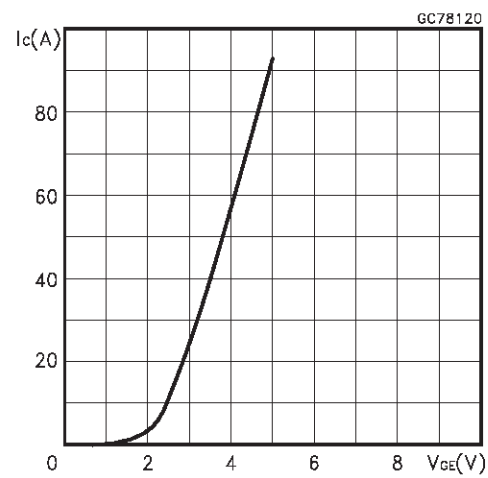
Thermal Impedance



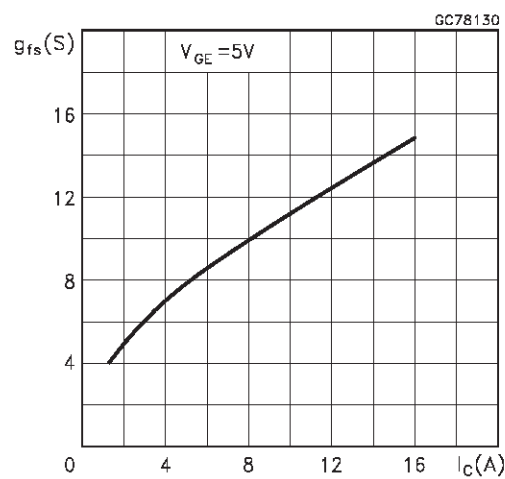
Output Characteristics



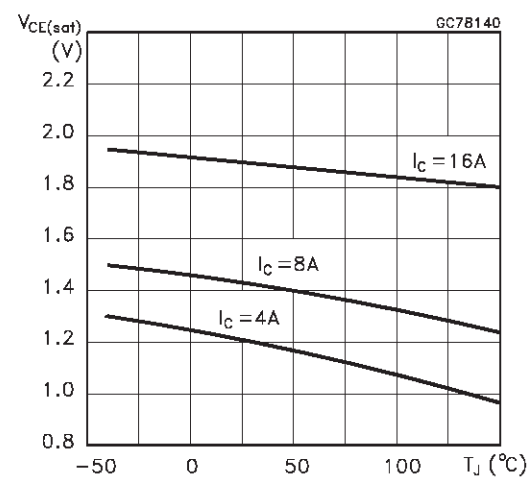
Transfer Characteristics



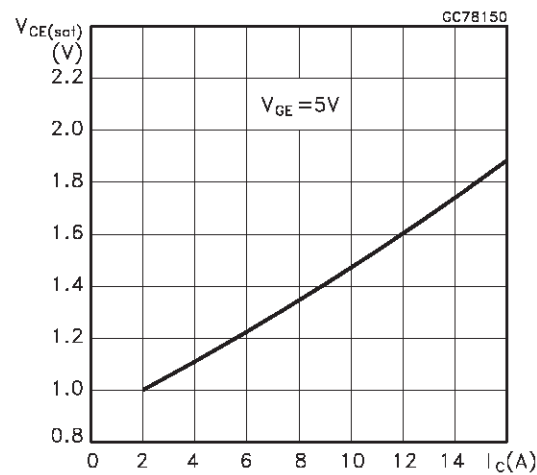
Transconductance



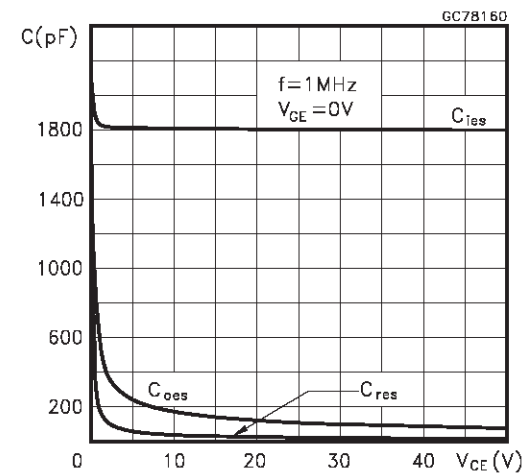
Collector-Emitter On Voltage vs Temperature



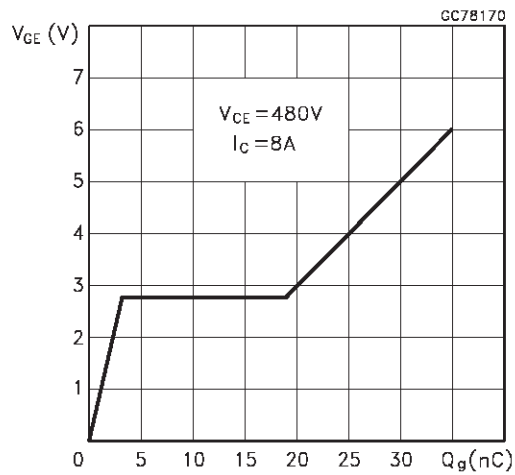
Collector-Emitter On Voltage vs Collector Current



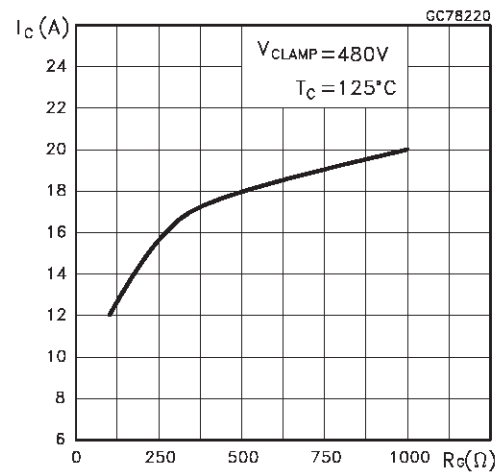
Capacitance Variations



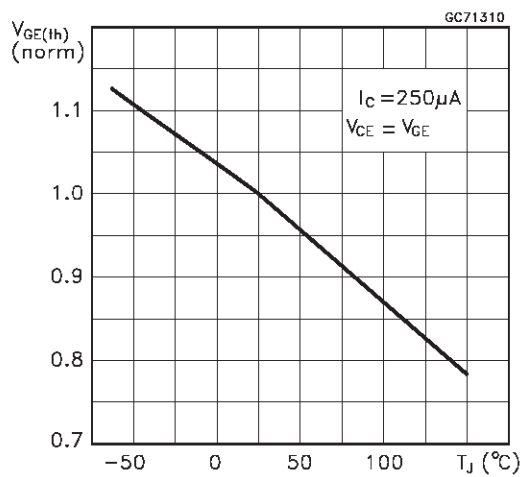
Gate Charge vs Gate-Emitter Voltage



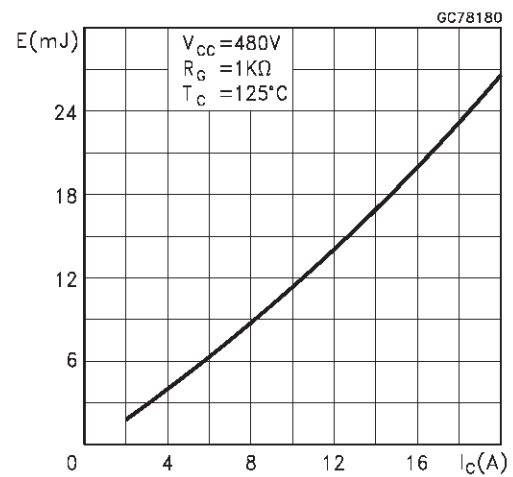
Latching Current vs R_g



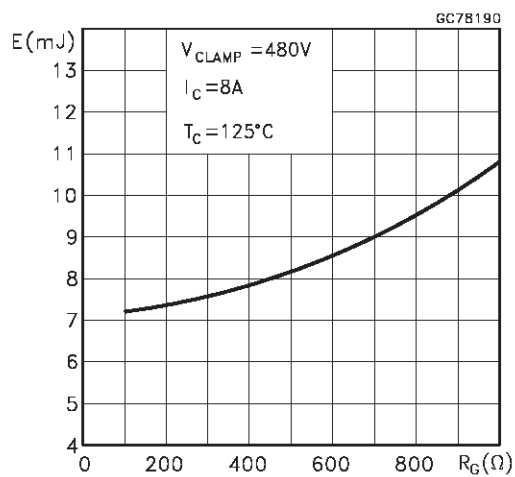
Gate Threshold vs Temperature



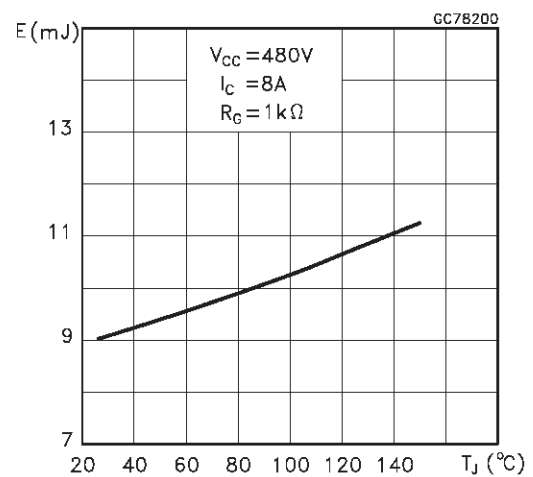
Off Losses vs Collector Current



Off Losses vs Gate Resistance



Off Losses vs Temperature



Switching Off Safe Operatin Area

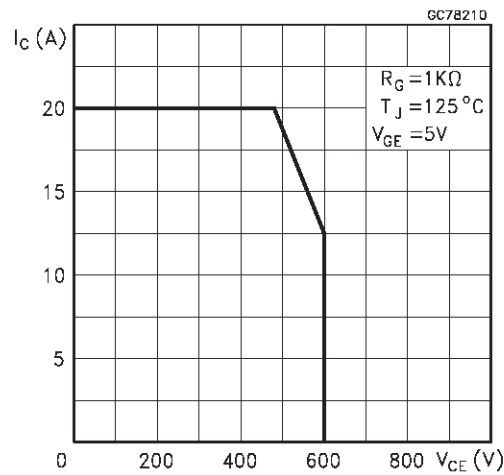


Fig. 1: Gate Charge test Circuit

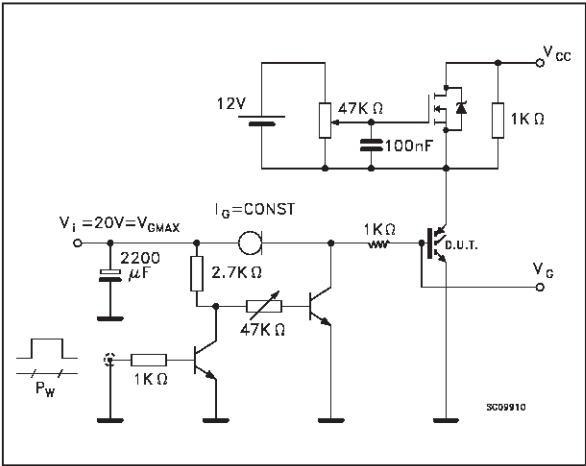


Fig. 2: Switching Times Test Circuit For Resistive Load

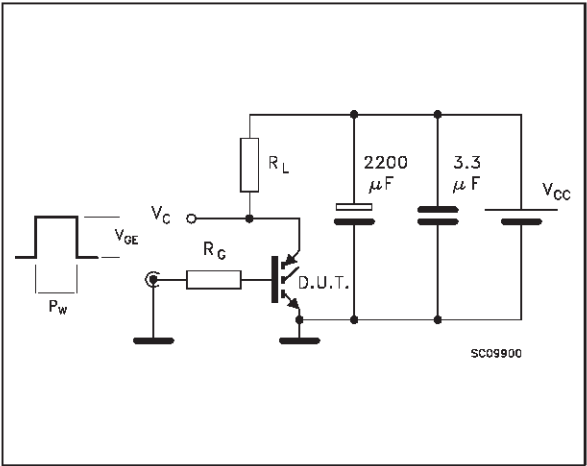
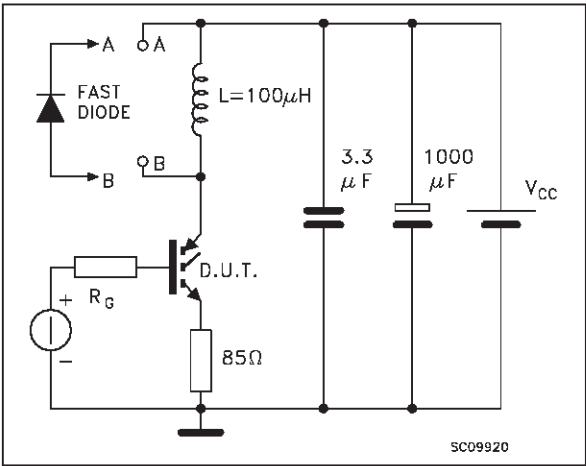
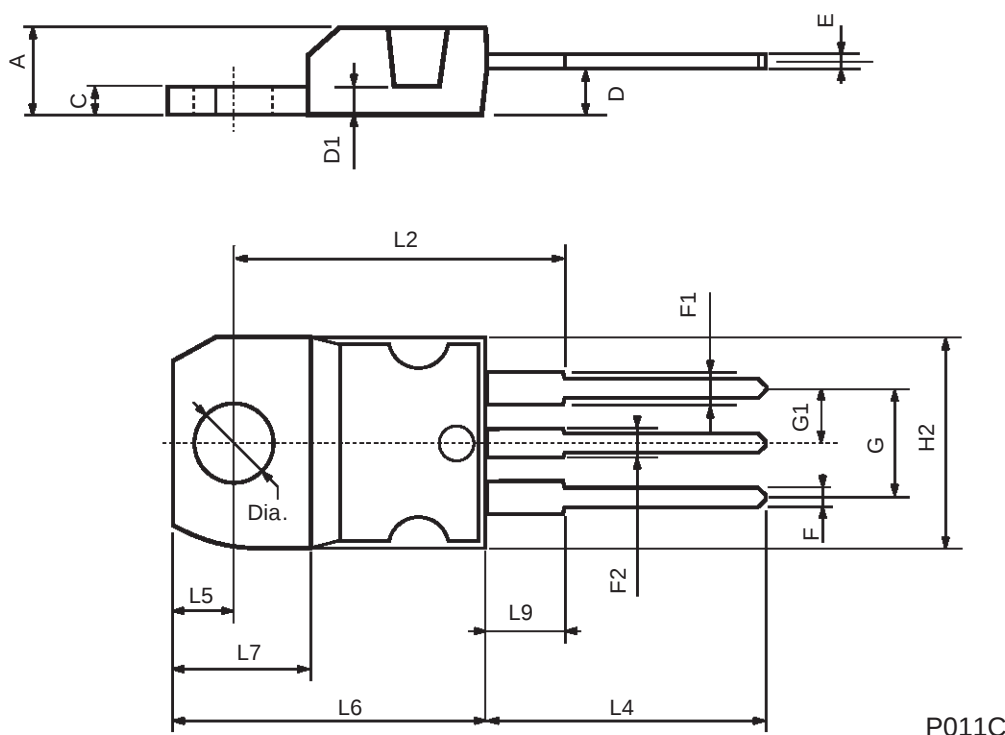


Fig. 3: Test Circuit For Inductive Load Switching



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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